

-12V_{DS} P-Channel Enhancement Mode MOSFET

Features

- $V_{DS}=-12V, I_D=-4A$
- $R_{DS(ON)}=45m\Omega$ (TYP.) $V_{GS}=4.5V$
- Reliable and Rugged
- Avalanche Rated
- Low On-Resistance



SOT-23



Applications

- Portable device
- Switch switching
- Load Switch
- Power management in portable/desktop PCs
- DC/DC conversion



Ordering Information

Device	Package		Marking	Package Qty.
AP2305BGN	SOT-23	Pb-Free	S5	3000pcs/Reel

Absolute Maximum Ratings (T_C=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V _{GS} =0V)	V _{DS}	-12	V
Gate-Source Voltage (V _{GS} =0V,static)	V _{GS}	±8	V
Continuous Drain Current (T _C =25°C)	I _D	-4	A
Pulsed Drain Current	I _S	0.8	A
Maximum Power Dissipation	P _D	0.4	W
Operating,Storage Temperature Range	T _J ,T _{STG}	-55~150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance,Junction-to-Case	R _{θJC}	-	60	-	°C/W
Thermal Resistance,Junction-to-Ambient	R _{θJA}	-	125	-	°C/W

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	-12	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$	-	-	1	μA
Gate -Source Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.7	1	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=3.5A$	-	30	50	m Ω
		$V_{GS}=2.5V, I_D=5A$	-	40	70	

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=15V$ $V_{GS}=0V$ $f=1MHz$	-	740	-	pF
Output capacitance	C_{oss}		-	290	-	
Reverse transfer capacitance	C_{rss}		-	190	-	
Gate Resistance	R_g	$f=1MHz$	-	7	-	Ω
Total Gate Charge	Q_g	$V_{DS}=15V$ $V_{GS}=4.5V$ $I_D=5.8A$	-	7.8	-	nC
Gate Source Charge	Q_{gs}		-	4.5	-	
Gate Drain Charge	Q_{gd}		-	1.2	-	
Turn-on delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=2.7\Omega$ $R_G=3\Omega$	-	13	-	ns
Rise time	t_r		-	35	-	
Turn-off delay Time	$t_{d(off)}$		-	32	-	
Fall time	t_f		-	10	-	

Reverse Diode Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=1A$	-	0.8	1.2	V

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